FKH6018A

N-Ch 60V Fast Switching MOSFETs

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

Green

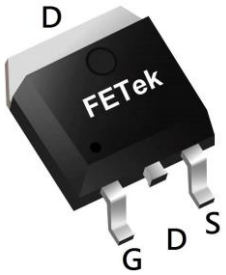
BVDSS	RDSON	ID
60V	8.2mΩ	98A

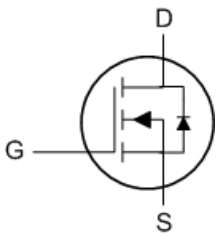
Description

The FKH6018A is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKH6018A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO263 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	98	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	62	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	11.5	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	9.2	A
I_{DM}	Pulsed Drain Current[2]	300	A
EAS	Single Pulse Avalanche Energy[3]	125	mJ
I_{AS}	Avalanche Current	50	A
P_D@T_C=25℃	Total Power Dissipation[4]	149	W
P_D@T_A=25℃	Total Power Dissipation[4]	2.02	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.84	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	6.5	8.2	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.5	---	4.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=30A	---	97	---	S
Q_g	Total Gate Charge (10V)	V_{DS}=48V , V_{GS}=10V , I_D=25A	---	35.5	---	nC
Q_{gs}	Gate-Source Charge		---	8.6	---	
Q_{gd}	Gate-Drain Charge		---	15.9	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω, I_D=30A	---	17.2	---	ns
T_r	Rise Time		---	33.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	28.0	---	
T_f	Fall Time		---	18.9	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1990	---	pF
C_{oss}	Output Capacitance		---	400	---	
C_{rss}	Reverse Transfer Capacitance		---	180	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	80	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=30A , dI/dt=100A/μs , T_J=25℃	---	11.9	---	nS
Q_{rr}	Reverse Recovery Charge		---	4.6	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=50A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

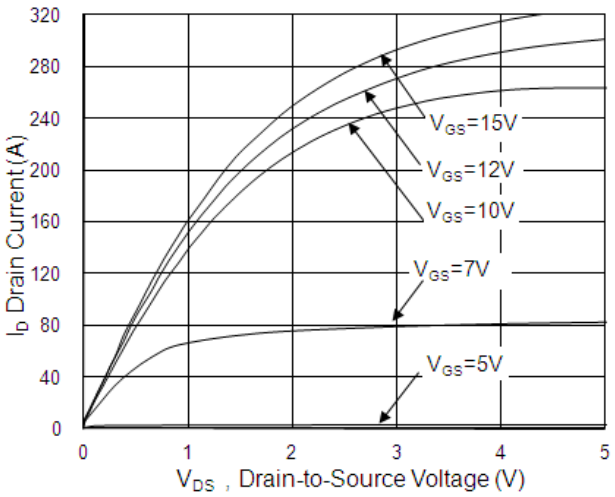


Fig.1 Typical Output Characteristics

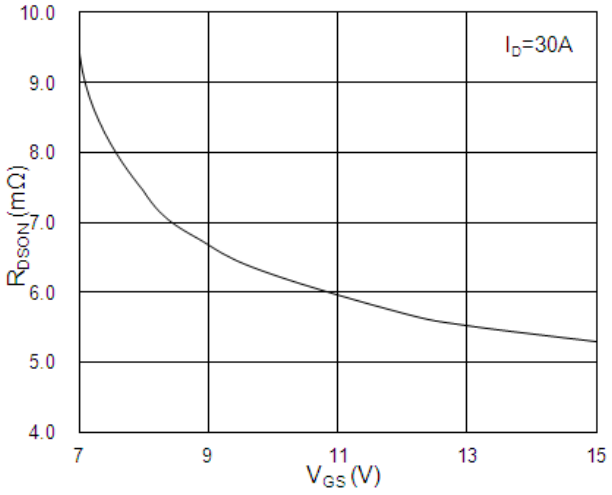


Fig.2 On-Resistance vs. G-S Voltage

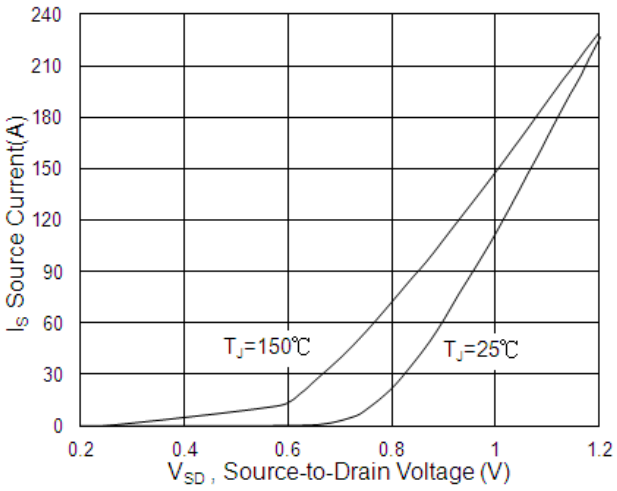


Fig.3 Source Drain Forward Characteristics

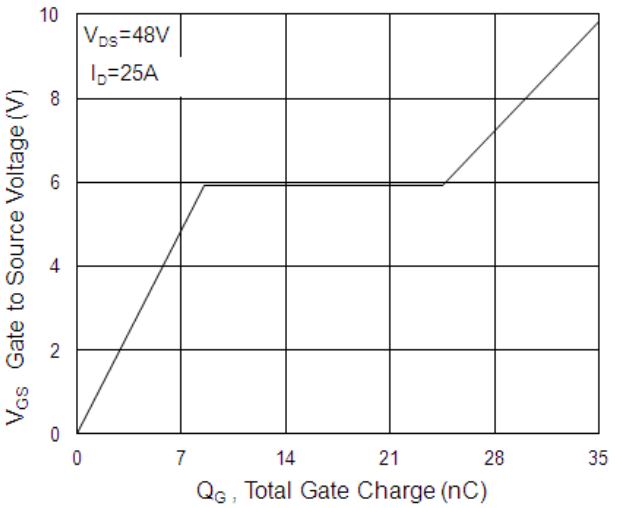


Fig.4 Gate-Charge Characteristics

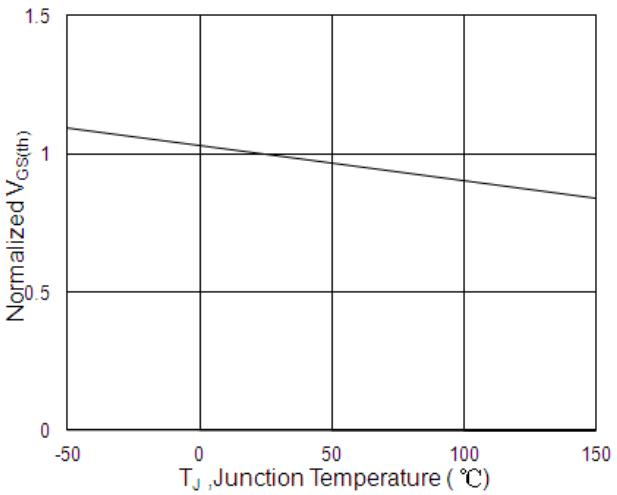


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

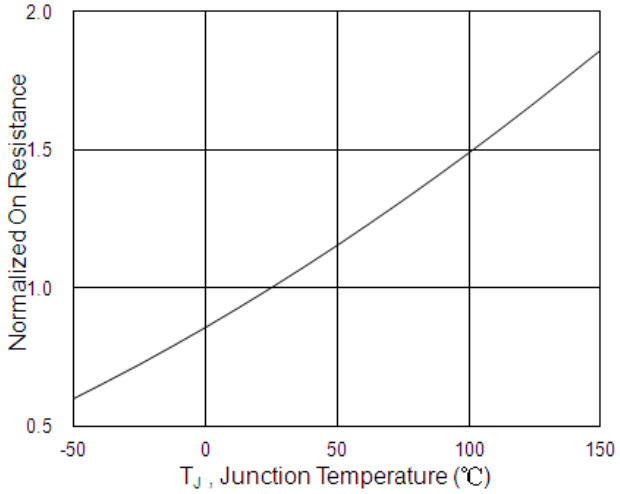


Fig.6 Normalized R_{DSON} vs. T_J

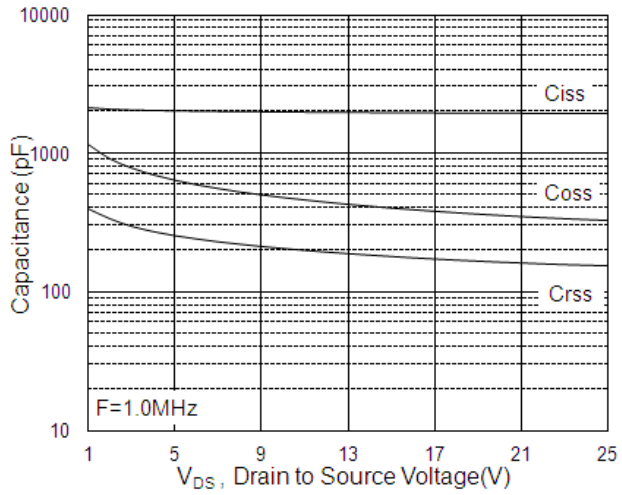


Fig.7 Capacitance

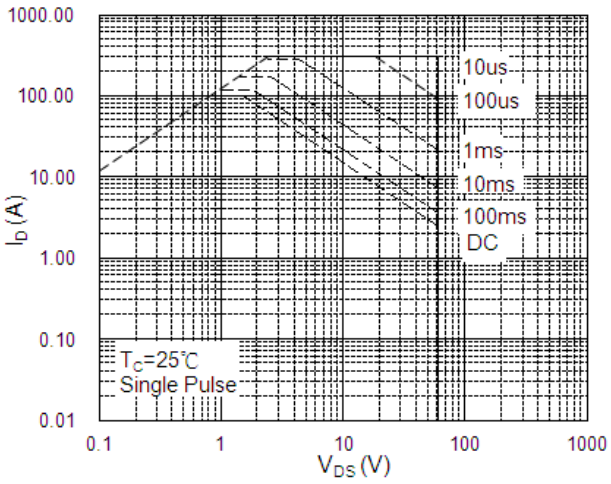


Fig.8 Safe Operating Area

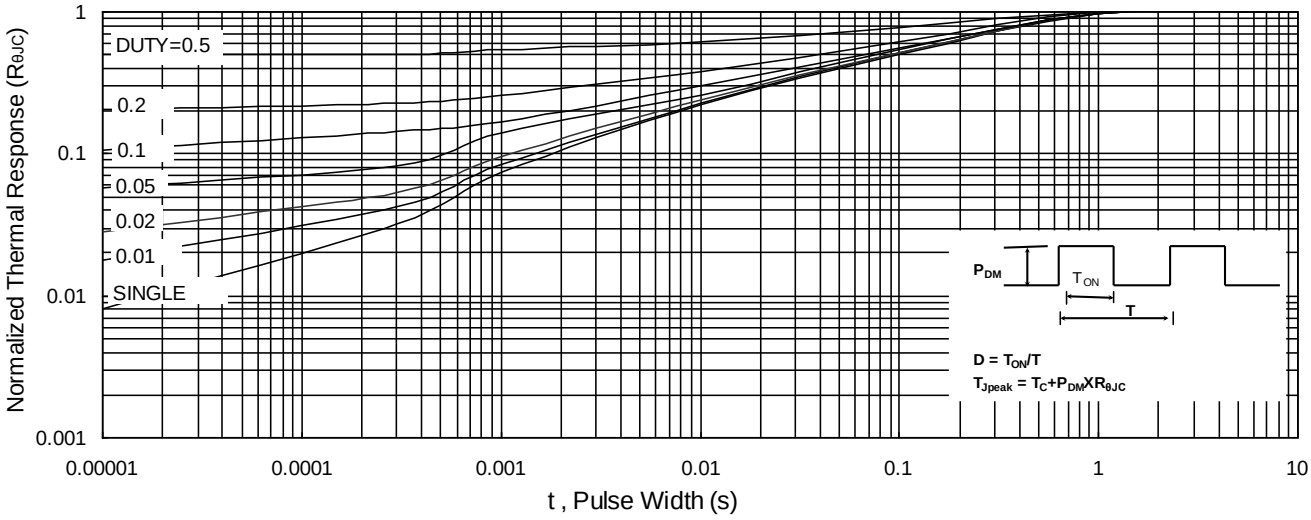


Fig.9 Normalized Maximum Transient Thermal Impedance

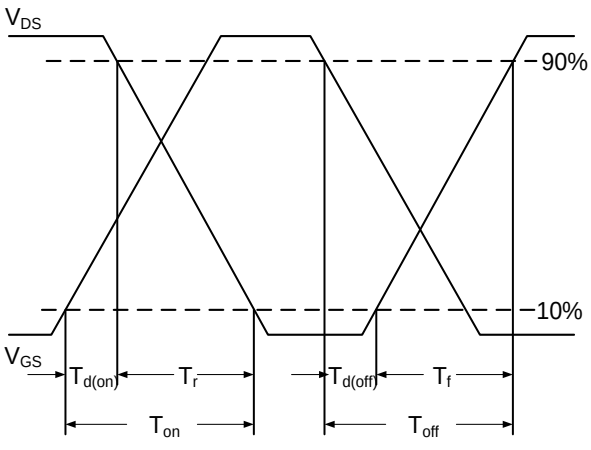


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

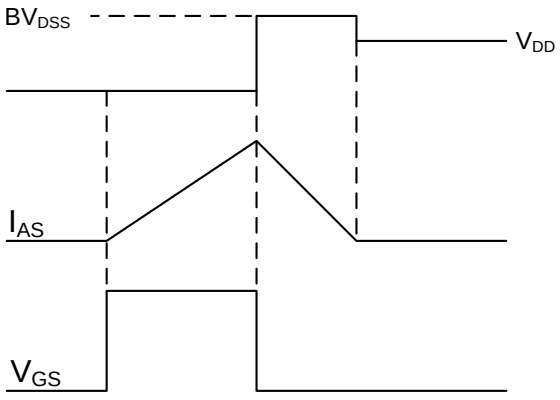
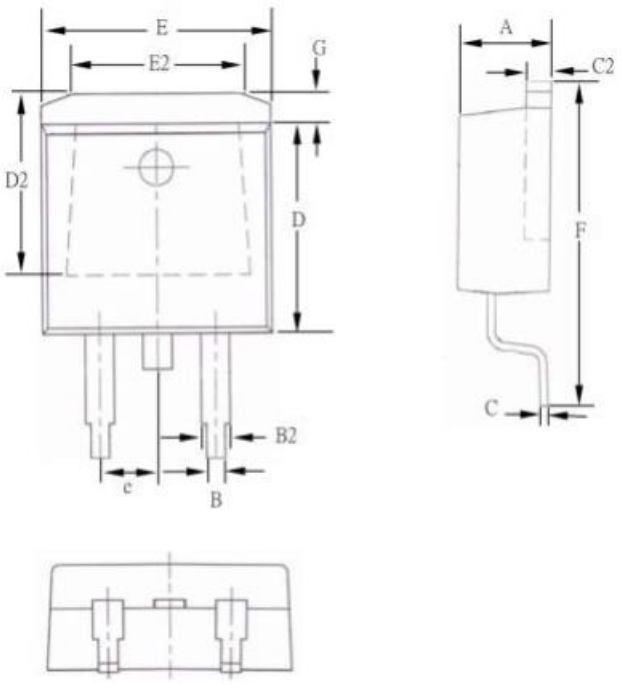


Fig.11 Unclamped Inductive Switching Waveform

TO263 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM		MIN	NOM	
A	4.06	—	4.83	0.160	—	0.190
B	0.51	—	0.99	0.020	—	0.039
B2	1.14	—	1.78	0.045	—	0.070
C	0.34	—	0.74	0.013	—	0.029
C2	1.14	—	1.65	0.045	—	0.065
D	8.38	—	9.65	0.330	—	0.380
D2	6.86	—	7.86	0.270	—	0.309
E	9.65	—	10.67	0.380	—	0.420
E2	6.22	—	7.40	0.245	—	0.291
F	13.08	—	15.50	0.515	—	0.610
G	0.68	—	1.68	0.027	—	0.066
e	—	2.54	—	—	0.100	—